

DESCRIPTION

Mitsubishi 2SA1530 is a super mini resin sealed silicon PNP epitaxial type transistor. It is designed for low frequency voltage amplify application.

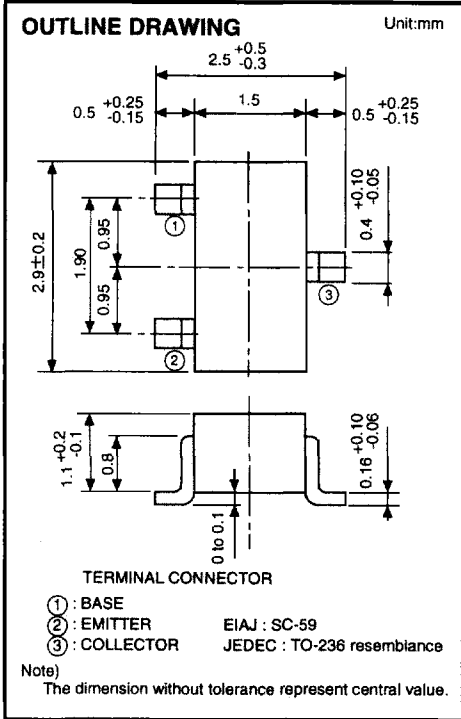
Complementary with 2SC3928.

FEATURE

- Small collector to emitter saturation voltage
 $V_{CE(sat)} = -0.3V \text{ max } (@ I_C = -30mA, I_B = -1.5mA)$
- Excellent linearity of DC forward current gain
- Super mini package for easy mounting

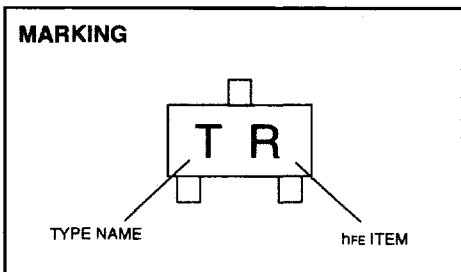
APPLICATION

For hybrid IC, small type machine low frequency voltage amplify application.



MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit
V _{CB0}	Collector to Base voltage	-50	V
V _{EB0}	Emitter to Base voltage	-6	V
V _{CE0}	Collector to Emitter voltage	-50	V
I _C	Collector current	-100	mA
P _C	Collector dissipation (Ta=25°C)	150	mW
T _J	Junction temperature	+125	°C
T _{stg}	Storage temperature	-55 to +125	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V _{(BR)CEO}	C to E break down voltage	I _C =-100 μA, R _{BE} =∞	-50			V
I _{CBO}	Collector cut off current	V _{CB} =-50V, I _E =0			-0.5	μA
I _{EB0}	Emitter cut off current	V _{EB} =-4V, I _C =0			-0.5	μA
h _{FE} *	DC forward current gain	V _{CE} =-6V, I _C =-1mA	120		820	—
h _{FE}	DC forward current gain	V _{CE} =-6V, I _C =-0.1mA	70			—
V _{CE(sat)}	C to E saturation voltage	I _C =-30mA, I _B =-1.5mA			-0.3	V
f _T	Gain band width product	V _{CE} =-6V, I _E =10mA		200		MHz
C _{ob}	Collector output capacitance	V _{CB} =-6V, I _E =0, f=1MHz		2.5		pF

* : It shows hFE classification in right table.

Item	Q	R	S	T
hFE	120 to 270	180 to 390	270 to 560	390 to 820
Marking	TQ	TR	TS	TT

TYPICAL CHARACTERISTICS

